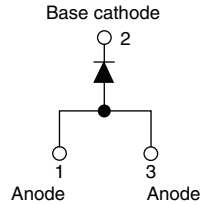




Input Rectifier Diode, 20 A



D²PAK



DESCRIPTION/FEATURES

The 20ETS...SPbF rectifier High Voltage Series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.



RoHS*
COMPLIANT

Typical applications are in input rectification and these products are designed to be used with Vishay HPP switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free.

PRODUCT SUMMARY	
V_F at 10 A	1 V
I_{FSM}	300 A
V_{RRM}	800/1200 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$, $T_J = 125\text{ °C}$ common heatsink of 1 °C/W	16.3	21	A

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Sinusoidal waveform	20	A
V_{RRM}		800/1200	V
I_{FSM}		300	A
V_F	20 A, $T_J = 25\text{ °C}$	1.1	V
T_J		- 40 to 150	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} AT 150 °C mA
20ETS08SPbF	800	900	1
20ETS12SPbF	1200	1300	

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	$T_C = 105\text{ °C}$, 180° conduction half sine wave	20	A
Maximum peak one cycle non-repetitive surge current	I_{FSM}	10 ms sine pulse, rated V_{RRM} applied	250	
		10 ms sine pulse, no voltage reapplied	300	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	316	A ² s
		10 ms sine pulse, no voltage reapplied	442	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	4420	A ² √s

* Pb containing terminations are not RoHS compliant, exemptions may apply

20ETS...SPbF High Voltage Series



Vishay High Power Products Input Rectifier Diode, 20 A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V_{FM}	20 A, $T_J = 25\text{ }^\circ\text{C}$		1.1	V
Forward slope resistance	r_t	$T_J = 150\text{ }^\circ\text{C}$		10.4	$\text{m}\Omega$
Threshold voltage	$V_{F(TO)}$			0.85	V
Maximum reverse leakage current	I_{RM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}$	0.1	mA
		$T_J = 150\text{ }^\circ\text{C}$		1.0	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}			- 40 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		1.3	$^\circ\text{C}/\text{W}$
Maximum thermal resistance, junction to ambient	$R_{thJA}^{(1)}$	For D ² PAK version		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased		0.5	
Approximate weight				2	g
				0.07	oz.
Mounting torque	minimum			6.0 (5.0)	kgf · cm (lbf · in)
	maximum			12 (10)	
Marking device		Case style D ² PAK (SMD-220)		20ETS08S	
				20ETS12S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 $^\circ\text{C}/\text{W}$
For recommended footprint and soldering techniques refer to application note #AN-994



20ETS...SPbF High Voltage Series

Input Rectifier Diode, 20 A Vishay High Power Products

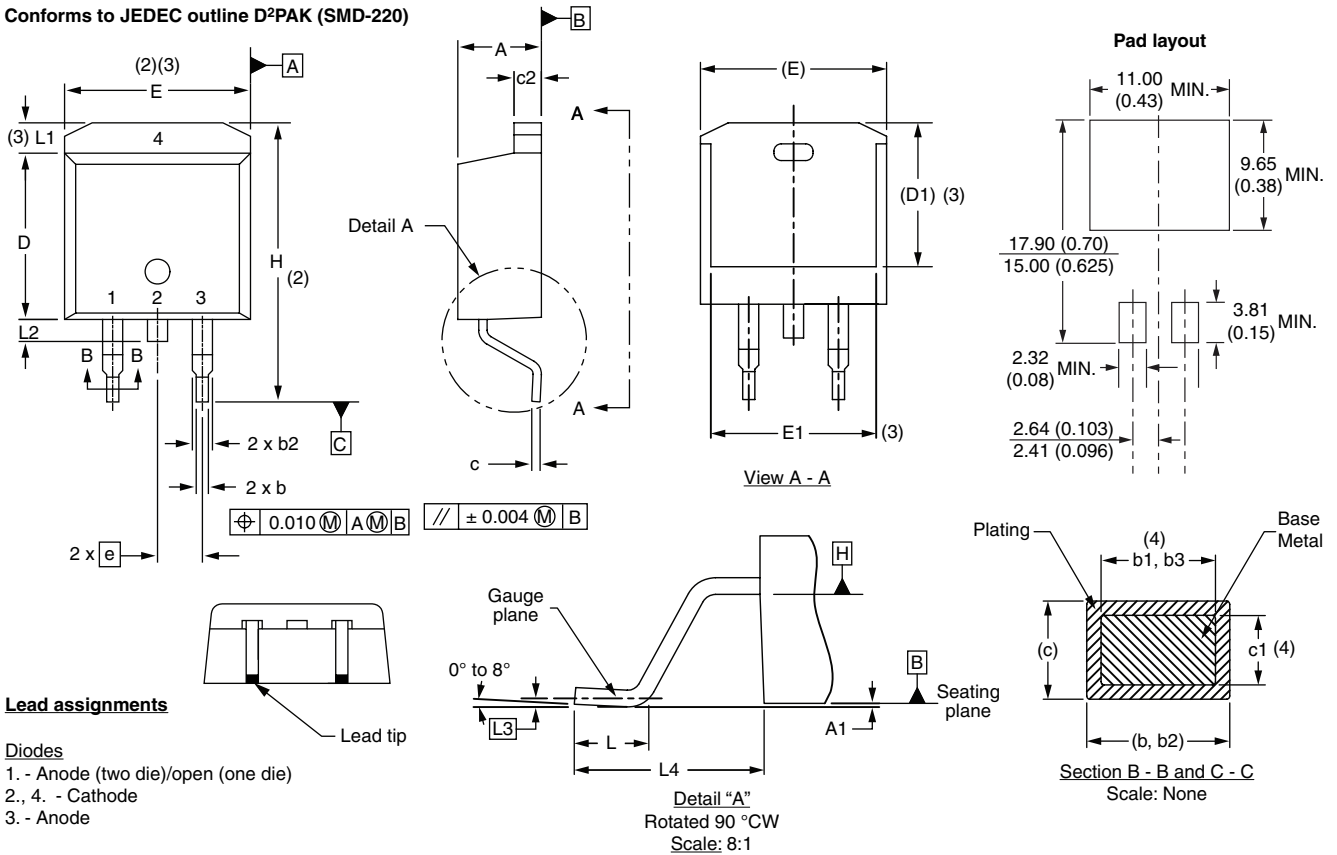
ORDERING INFORMATION TABLE

Device code	20	E	T	S	12	S	TRL	PbF
	①	②	③	④	⑤	⑥	⑦	⑧
①	-	Current rating (20 = 20 A)						
②	-	Circuit configuration E = Single diode						
③	-	Package: T = TO-220AC						
④	-	Type of silicon: S = Standard recovery rectifier						
⑤	-	Voltage code x 100 = V_{RRM}						08 = 800 V 12 = 1200 V
⑥	-	S = TO-220 D ² PAK (SMD-220) version						
⑦	-	• None = Tube • TRL = Tape and reel (left oriented) • TRR = Tape and reel (right oriented)						
⑧	-	• None = Standard production • PbF = Lead (Pb)-free						

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC outline D²PAK (SMD-220)



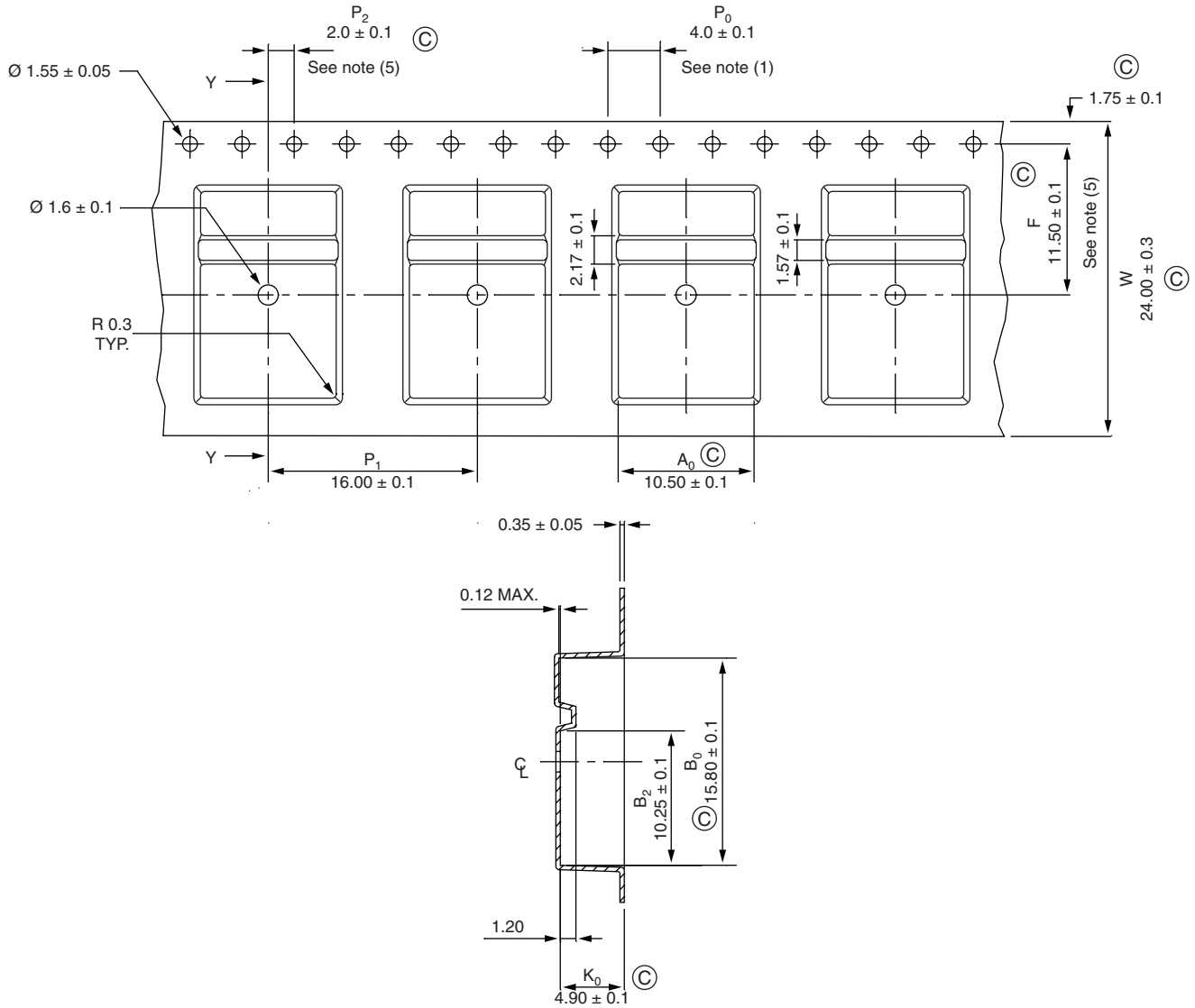
SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	-	0.270	-	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	6.22	-	0.245	-	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

D²PAK

TAPE AND REEL INFORMATION in millimeters (inches)



Section Y - Y

Notes

- (1) 10 sprocket hole pitch cumulative tolerance ± 0.02
- (2) Camber not to exceed 1 mm in 100 mm
- (3) Material: conductive black styrenic alloy
- (4) K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier
- (5) Measured from centerline of sprocket hole to centerline of pocket
- (6) Vendor: (optional)
- (7) Must also meet requirements of EIA standard # EIA-481A taping of surface mount components for automatic placement
- (8) Surface resistivity of molded material must measure less or equal to $10^6 \Omega$ per square. Measured in accordance to procedure given in ASTM D-257 and ASTM D-991
- (9) Total length per reel must be 45 m
- (10) C critical